M Ãakmak

List of Publications by Year
in descending order

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94	831	566801	610482
papers	citations	15 h-index	24 g-index

94	94	94	935
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Charge density wave in a SnSe₂ layer on and the effect of surface hydrogenation. Physical Chemistry Chemical Physics, 2022, 24, 6820-6827.	1.3	0
2	The currentâ€“voltage characteristics of V2O5/n-Si Schottky diodes formed with different metals. Journal of Materials Science: Materials in Electronics, 2021, 32, 20284-20294.	1.1	5
3	Biaxial Strain-Induced Electronic Structure and Optical Properties of SiP$$_{2}$$S Monolayer. Journal of Electronic Materials, 2021, 50, 6253-6260.	1.0	11
4	Electronic, phononic and superconducting properties of trigonal Li₂ MSi₂ (M) Tj ETQq0 0 0 rgBT /Overlock 10	0.7	2
5	A Comprehensive Study on a Stand-Alone Germanium (Ge) Solar Cell. Journal of Electronic Materials, 2020, 49, 1249-1256.	1.0	5
6	Thickness-dependent physical properties of sputtered V2O5 films and Ti/V2O5/n-Si Schottky barrier diode. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	6
7	Quantum-well states for uniform Ag layers on the Ga-induced Si(111)â€“(3Ã—3)R30Â° surface. Surface Science, 2020, 701, 121684.	0.8	0
8	Adsorption of S on Si(111) with M4ÂÃ—Â4 superstructure. Surface Science, 2020, 701, 121694.	0.8	0
9	Atomic and electronic structures of Sn covered W(110) surface. European Physical Journal B, 2020, 93, 1.	0.6	3
10	Electronic structure of the Pd2Sn surface alloy on Pd(111)-(âˆš3 Ã— âˆš3)R30Â°. European Physical Journal B, 2019, 92, 1.	0.6	3
11	Tl on the Si(111)- surface: Density Functional Theory. Philosophical Magazine, 2019, 99, 1656-1668.	0.7	1
12	Electronic structure, phonon and superconductivity for WP 5d-transition metal. Journal of Applied Physics, 2019, 126, 175103.	1.1	9
13	Co on the H-passivated Si(001) surface: Density-functional calculations. Physica B: Condensed Matter, 2018, 542, 44-50.	1.3	1
14	Characterization of AlInN/AlN/GaN Heterostructures with Different AlN Buffer Thickness. Journal of Electronic Materials, 2016, 45, 3278-3284.	1.0	6
15	Alkali and Alkaline earth metal doped aluminum tetraborides containing intrinsic planar boron sheet: XAlB4 (X= Li, Mg, Ca, and Na). Computational Materials Science, 2016, 124, 130-141.	1.4	5
16	Structural and electronic properties of AB- and AA-stacking bilayer-graphene intercalated by Li, Na, Ca, B, Al, Si, Ge, Ag, and Au atoms. Solid State Communications, 2016, 231-232, 57-63.	0.9	15
17	Surface structure and photoluminescence properties of AZO thin films on polymer substrates. Surface and Interface Analysis, 2015, 47, 93-98.	0.8	37
18	Influence of substrate temperature on structural and optical properties of RF sputtered ZnMnO thin films. Semiconductors, 2015, 49, 780-784.	0.2	0

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19	AZO thin film-based UV sensors: effects of RF power on the films. Applied Physics A: Materials Science and Processing, 2015, 119, 965-970.	1.1	24
20	Fabrication and characterization of electrodeposited and magnetron-sputtered thin films. International Journal of Computational Methods and Experimental Measurements, 2015, 3, 165-174.	0.1	5
21	Theoretical investigation of charge accumulation layer on the Bi-induced InAs(111)-(2â€‰Ã—â€‰2) surface. Journal of Applied Physics, 2014, 115, 163702.	1.1	0
22	Ab initio study of Tl on Si(111)-(3Ã—1) surface. Physica Status Solidi (B): Basic Research, 2014, 251, 1570-1573.	0.7	4
23	Effect of film thickness on properties of aluminum doped zinc oxide thin films deposition on polymer substrate. Journal of Materials Science: Materials in Electronics, 2013, 24, 5091-5096.	1.1	20
24	Effects of high-temperature AlN buffer on the microstructure of AlGaN/GaN HEMTs. Semiconductors, 2013, 47, 820-824.	0.2	13
25	Passivation effect of allylamine molecule on the electronic structure of a Si(001)â”(2Ã—1) surface. Surface Science, 2012, 606, 470-474.	0.8	3
26	The influence of thickness and ammonia flow rate on the properties of AlN layers. Materials Science in Semiconductor Processing, 2012, 15, 32-36.	1.9	20
27	Effects of Thermal Annealing and Film Thickness on the Structural and Morphological Properties of Titanium Dioxide Films. Acta Physica Polonica A, 2012, 121, 247-248.	0.2	15
28	Photocontrollable DNA hybridization on reversibly photoresponsive surfaces. Journal of Materials Chemistry, 2011, 21, 10415.	6.7	13
29	Molecular design of photoswitchable surfaces with controllable wettability. Journal of Materials Chemistry, 2011, 21, 3189.	6.7	31
30	Atomic and electronic properties of P/Si(1Â1Â1)-(2ÂÃ—Â1) surface. EPJ Applied Physics, 2011, 56, 31302.	0.3	1
31	Characterization of an AlN buffer layer and a thick-GaN layer grown on sapphire substrate by MOCVD. Journal of Materials Science, 2011, 46, 1606-1612.	1.7	15
32	Adsorption of Sn on the Ge(111)â€(3â€‰Ã—â€‰3) surface studied by ab initio density functional theory. Physica Status Solidi (B): Basic Research, 2011, 248, 2142-2146.	0.7	1
33	Structural investigation and electronic band transitions of nanostructured TiO₂ thin films. Crystal Research and Technology, 2011, 46, 1207-1214.	0.6	11
34	Electronic and structural properties of armchair SWCNT/TiO2(110)-(1Ã—2) system. Surface Science, 2011, 605, 593-596.	0.8	2
35	Understanding 4-bromostyrene Adsorption on the Si(001)-(1Ã—2) surface: A density functional theory study. Surface Science, 2011, 605, 1056-1061.	0.8	1
36	Atomic and electronic properties of tert-butanol on the Si(001)-(2Ã—1) surface. European Physical Journal B, 2010, 76, 359-363.	0.6	2

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37	Adsorption of S, O, and H on the NiAl(110)-(2Ã—2) surface. Physica B: Condensed Matter, 2010, 405, 4059-4063.	1.3	12
38	Ab initio study of Yb on the Ge(111)â€“(3Ã—2) and Si(111)â€“(3Ã—2) surfaces. Surface Science, 2010, 604, 1899-1905.	0.8	2
39	Firstâ€principle studies of dissociative adsorption of H₂O on NiAl(110)â€(2 Ã— 2) surface. Surface and Interface Analysis, 2010, 42, 1326-1329.	0.8	3
40	Atomic and electronic structure of S-terminated GaAs(001) surface. Journal of Applied Physics, 2010, 108, 063713.	1.1	3
41	The confined random walks in two-dimensional bounded domain. Europhysics Letters, 2009, 87, 60003.	0.7	1
42	Effect of hydrogenation on the electronic structure of the P/Si(0 0 1)-(1 Ã— 2) surface. Surface Science, 2009, 603, 2271-2275.	0.8	1
43	Effects of thermal annealing on the morphology of the AlxGa(1â^'x)N films. Materials Science in Semiconductor Processing, 2009, 12, 238-242.	1.9	8
44	Atomic and electronic structure of group-IV adsorbates on the GaAs(001)-(1Ã—2) surface. Surface Science, 2009, 603, 2683-2687.	0.8	3
45	Atomic and electronic properties of furan on the Si(001)-(2Ã—2) surface. Surface Science, 2008, 602, 2845-2848.	0.8	5
46	The profile of temperature and voltage dependent series resistance and the interface states in (Ni/Au)/Al0.3Ga0.7N/AlN/GaN heterostructures. Microelectronic Engineering, 2008, 85, 2316-2321.	1.1	25
47	Atomic and electronic structures of Tl/Si(111)-. Surface Science, 2008, 602, 1376-1380.	0.8	12
48	Effect of Bleaching on Roughness of Dental Composite Resins. Journal of Adhesion, 2008, 84, 897-914.	1.8	7
49	Atomic and electronic structure of Bi/GaAs(001)-Î±2(2 Ã— 4). Journal of Physics Condensed Matter, 2008, 20, 265003.	0.7	6
50	Atomic and electronic structures of the group-IV elements on Si(111)-(â^š3 Ã— â^š3) surface. Journal of Physics: Conference Series, 2008, 100, 072025.	0.3	2
51	Surface Morphology of Al0.3Ga0.7N/Al2O3-High Electron Mobility Transistor Structure. Journal of Nanoscience and Nanotechnology, 2008, 8, 640-644.	0.9	7
52	Role of Local Density Approximation in structure and electronic properties of InxGa1â^'xAs alloys. AIP Conference Proceedings, 2007, , .	0.3	0
53	Identification ofGe/SiIntermixing Processes at theBi/Ge/Si(111)Surface. Physical Review Letters, 2007, 98, 166104.	2.9	21
54	The behavior of the I-V-T characteristics of inhomogeneous (Niâ^•Au)â€“Al0.3Ga0.7Nâ^•AlNâ^•GaN heterostructures at high temperatures. Journal of Applied Physics, 2007, 102, .	1.1	74

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55	Structural, morphological, and optical properties of AlGaN/GaN heterostructures with AlN buffer and interlayer. Journal of Applied Physics, 2007, 101, 123502.	1.1	40
56	Binding Formation of 12-Hydroxydodecanoic Acid on Si(001)-(2 Ã— 2). Journal of Physical Chemistry C, 2007, 111, 4375-4378.	1.5	3
57	Chemisorption of 3-Aminopropyltrimethoxysilane on Si(001)-(2 Ã— 2). Journal of Physical Chemistry C, 2007, 111, 15020-15025.	1.5	10
58	Effect of Molecular and Electronic Structure on the Light-Harvesting Properties of Dye Sensitizers. Journal of Physical Chemistry C, 2007, 111, 7539-7547.	1.5	22
59	An ab initio study of 3-aminopropyltrimethoxysilane molecule on Si(111)-() surface. Surface Science, 2007, 601, 3740-3744.	0.8	10
60	Chemisorption of 4-(4-amino-phenylazo) benzoic acid molecule on the Si(001)-(4Ã—2) surface. Surface Science, 2007, 601, 3760-3764.	0.8	4
61	Structural and optical properties of an InxGa1â^'xN/GaN nanostructure. Surface Science, 2007, 601, 3892-3897.	0.8	10
62	Construction of a novel multilayer system and its use for oriented immobilization of immunoglobulin G. Surface Science, 2007, 601, 4563-4570.	0.8	15
63	Effect of hydrogenation on P/Si(001)-(1Ã—2). Surface Science, 2007, 601, 1489-1493.	0.8	3
64	Effect of hydrogenation on B/Si(001)-(1Ã—2). Surface Science, 2007, 601, 3711-3716.	0.8	2
65	Atomic and electronic structure of Sr/Si(001)-(2Ã—2). Surface Science, 2006, 600, 3614-3618.	0.8	5
66	Desorption site-specificity and halogen minority sites on Si(1 1 1). New Journal of Physics, 2005, 7, 208-208.	1.2	6
67	Ab Initio Calculation of Hyperfine Interaction Parameters: Recent Evolutions, Recent Examples. , 2005, , 9-18.		0
68	Coordination-dependence of hyperfine interactions at impurities on fcc metal surfaces. II. Magnetic hyperfine field. Physical Review B, 2004, 70, .	1.1	16
69	Coordination dependence of hyperfine interactions at impurities on fcc metal surfaces. I. Electric-field gradient. Physical Review B, 2004, 70, .	1.1	27
70	Ab Initio Calculation of Hyperfine Interaction Parameters: Recent Evolutions, Recent Examples. Hyperfine Interactions, 2004, 158, 9-18.	0.2	4
71	An ab initio study of the Te surfactant on Ge/Si(001). Surface Science, 2004, 566-568, 719-722.	0.8	1
72	Ab initio study of the adsorption of In on the Ge(001) surface. Surface Science, 2004, 566-568, 931-936.	0.8	8

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73	Ab initio study of the one-monolayer Sb/Ge interface. Surface Science, 2004, 566-568, 956-960.	0.8	3
74	Theoretical study of dangling-bond wires on the H-terminated Si surface. Surface Science, 2003, 532-535, 556-559.	0.8	11
75	Ab initio study of the one-monolayer Sb/Si(001) interface. Surface Science, 2003, 532-535, 661-665.	0.8	5
76	Adsorption of Te on Ge(001): Density-functional calculations. Physical Review B, 2003, 67, .	1.1	5
77	Ab initio study of the adsorption of In on the Si(001)-(2Ã—2) surface. Surface Science, 2002, 507-510, 23-28.	0.8	3
78	Ab initio study of the adsorption and desorption of Se on the Si() surface. Surface Science, 2002, 507-510, 29-33.	0.8	6
79	Segregation and non-segregation of Ge for H(Cl):Si()/Ge-(2Ã—1) and H(Cl):Si()/Ge-(3Ã—1). Surface Science, 2002, 507-510, 40-45.	0.8	2
80	Adsorption of GeH2 on the bare and hydrogenated Ge(001) surfaces. Vacuum, 2002, 67, 21-25.	1.6	1
81	Adsorption of GeH2 on the Si(001) surface. Surface Science, 2001, 482-485, 26-31.	0.8	3
82	Effect of hydrogenation on the adsorption ofGeonSi(001). Physical Review B, 2001, 64, .	1.1	4
83	Dissociative adsorption ofSi2H6on the Si(001) surface. Physical Review B, 2000, 61, 10216-10222.	1.1	34
84	Structure and energetics of segregated and non-segregated H:Ge(001)/Si and Cl:Ge(001)/Si. Surface Science, 2000, 454-456, 166-171.	0.8	10
85	Comparative study of Bi overlayers on III-Sb(110) (1Ã—1) surfaces. Surface Science, 2000, 454-456, 26-29.	0.8	1
86	Adsorption of partially and fully dissociatedH2Smolecules on the Si(001) and Ge(001) surfaces. Physical Review B, 1999, 60, 5497-5505.	1.1	25
87	Ab-initio study of the adsorption of H2S onto the Si(001) surface. Surface Science, 1999, 433-435, 420-424.	0.8	2
88	Structural, electronic and vibrational properties of the InSb(110) surface. Applied Surface Science, 1998, 123-124, 146-150.	3.1	5
89	An ab initio calculation of the adsorption of H2S onto InP(110)-(1 Ã— 1) surface. Applied Surface Science, 1998, 123-124, 52-55.	3.1	5
90	Theoretical study of the GaAs(110)-(1Ã—1)â€“H2S surface. Surface Science, 1998, 402-404, 658-662.	0.8	1

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91	Ab initiostudy of atomic geometry, electronic states, and bonding for H2S adsorption on III-V semiconductor (110)-(1Å—1)surfaces. Physical Review B, 1998, 57, 4486-4492.	1.1	15
92	Adsorption and desorption of S on and off Si(001) studied by ab initio density functional theory. Journal of Applied Physics, 1998, 84, 6070-6075.	1.1	16
93	Calculation of atomic geometry, electronic states, and bonding for the S-deposited InP(110) surface. Physical Review B, 1997, 56, 1928-1935.	1.1	6
94	A theoretical study of sulphur adsorption on InP(110). Surface Science, 1997, 377-379, 592-596.	0.8	0